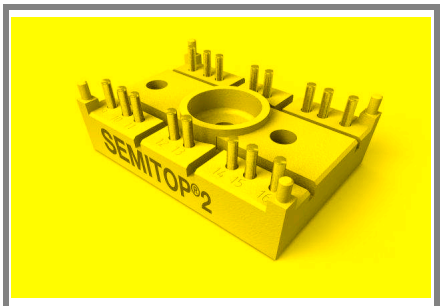
SK25GB12T4



SEMITOP® 2

IGBT Module

SK25GB12T4

Target Data

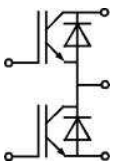
Features

- One screw mounting module
- Trench4 IGBT technology
- CAL4 technology FWD

Typical Applications*

Remarks

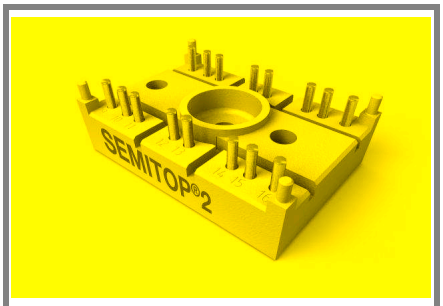
- $V_{CE,sat}$, V_F = chip level value



GB

Absolute Maximum Ratings	T_s = 25 °C, unless otherwise specified			
Symbol	**Conditions**		**Values**	**Units**
IGBT				
V_{CES}	T_j = 25 °C		1200	V
I_C	T_j = 175 °C	T_s = 25 °C	37	A
		T_s = 70 °C	30	A
I_{CRM}	I_{CRM}= 3 x I_{Cnom}		75	A
V_{GES}			± 20	V
t_{psc}	V_{CC} = 800 V; $V_{GE} \leq$ 15 V; V_{CES} < 1200 V	T_j = 150 °C	10	µs
Inverse Diode				
I_F	T_j = 175 °C	T_s = 25 °C	30	A
		T_s = 70 °C	25	A
I_{FRM}	I_{FRM}= 3 x I_{Fnom}		75	A
I_{FSM}	t_p = 10 ms; half sine wave	T_j = 150 °C	160	A
Module				
$I_{t(RMS)}$				A
T_{vj}			-40 ... +175	°C
T_{stg}			-40 ... +125	°C
V_{isol}	AC, 1 min.		2500	V

Characteristics	T_s = 25 °C, unless otherwise specified					
Symbol	**Conditions**		**min.**	**typ.**	**max.**	**Units**
IGBT						
$V_{GE(th)}$	V_{GE} = V_{CE}, I_C = 0,85 mA		5	5,8	6,5	V
I_{CES}	V_{GE} = 0 V, V_{CE} = V_{CES}	T_j = 25 °C			0,0024	mA
		T_j = 125 °C				mA
I_{GES}	V_{CE} = 0 V, V_{GE} = 20 V	T_j = 25 °C			120	nA
		T_j = 125 °C				nA
V_{CE0}		T_j = 25 °C		1,1	1,3	V
		T_j = 150 °C		1	1,2	V
r_{CE}	V_{GE} = 15 V	T_j = 25°C		30		mΩ
		T_j = 150°C		50		mΩ
$V_{CE(sat)}$	I_{Cnom} = 25 A, V_{GE} = 15 V	T_j = 25°C$_{chiplev.}$		1,85	2,05	V
		T_j = 150°C$_{chiplev.}$		2,25	2,45	V
C_{ies}	V_{CE} = 25, V_{GE} = 0 V	f = 1 MHz		1,43		nF
C_{oes}				0,115		nF
C_{res}				0,085		nF
Q_G	V_{GE}=-7V...+15V			137,5		nC
$t_{d(on)}$	R_{Gon} = 19 Ω di/dt = 2825 A/µs	V_{CC} = 600V I_C= 25A T_j = 150 °C V_{GE}= -7/+15V		22		ns
t_r				19,5		ns
E_{on}				2,27		mJ
$t_{d(off)}$	R_{Goff} = 19 Ω di/dt = 2825 A/µs			288		ns
t_f				77,5		ns
E_{off}				2,7		mJ
$R_{th(j-s)}$	per IGBT			1,31		K/W



SEMITOP® 2

IGBT Module

SK25GB12T4

Target Data

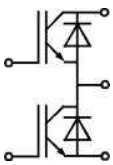
Features

- One screw mounting module
- Trench4 IGBT technology
- CAL4 technology FWD

Typical Applications*

Remarks

- $V_{CE,sat}$, V_F = chip level value



GB

Characteristics						
Symbol	**Conditions**		**min.**	**typ.**	**max.**	**Units**
Inverse Diode						
$V_F = V_{EC}$	I_{Fnom} = 25 A; V_{GE} = 0 V	T_j = 25 °$C_{chiplev.}$		2,4	2,62	V
		T_j = 150 °$C_{chiplev.}$		2,45	2,8	V
V_{F0}		T_j = 25 °C		1,3	1,5	V
		T_j = 150 °C		0,9	1,1	V
r_F		T_j = 25 °C		44	45	mΩ
		T_j = 150 °C		62	68	mΩ
I_{RRM}	I_F = 25 A	T_j = 150 °C		31,5		A
Q_{rr}	di/dt = 2825 A/µs			1,15		µC
E_{rr}	V_{CC}= 600V			1,28		mJ
$R_{th(j-s)D}$	per diode			1,91		K/W
M_s	to heat sink		2,25		2,5	Nm
w				30		g

This is an electrostatic discharge sensitive device (ESDS), international standard IEC 60747-1, Chapter IX.

* The specifications of our components may not be considered as an assurance of component characteristics. Components have to be tested for the respective application. Adjustments may be necessary. The use of SEMIKRON products in life support appliances and systems is subject to prior specification and written approval by SEMIKRON. We therefore strongly recommend prior consultation of our personal.

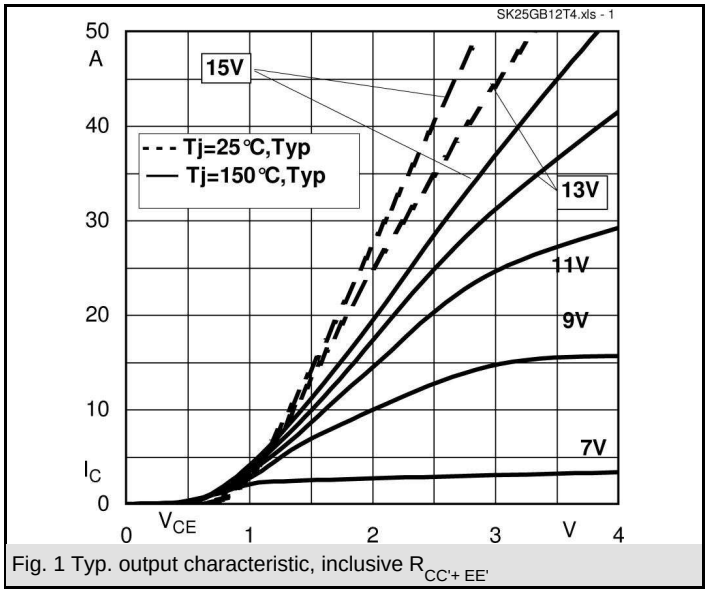


Fig. 1 Typ. output characteristic, inclusive $R_{CC'+EE'}$

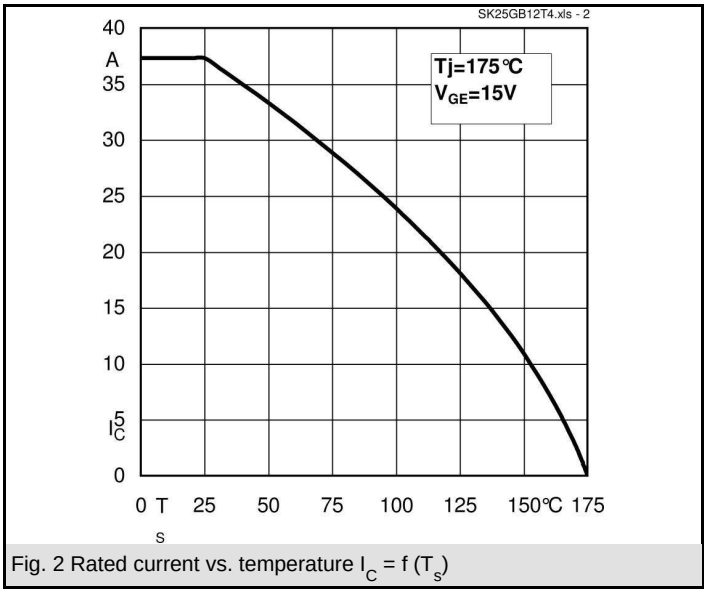


Fig. 2 Rated current vs. temperature $I_C = f(T_s)$

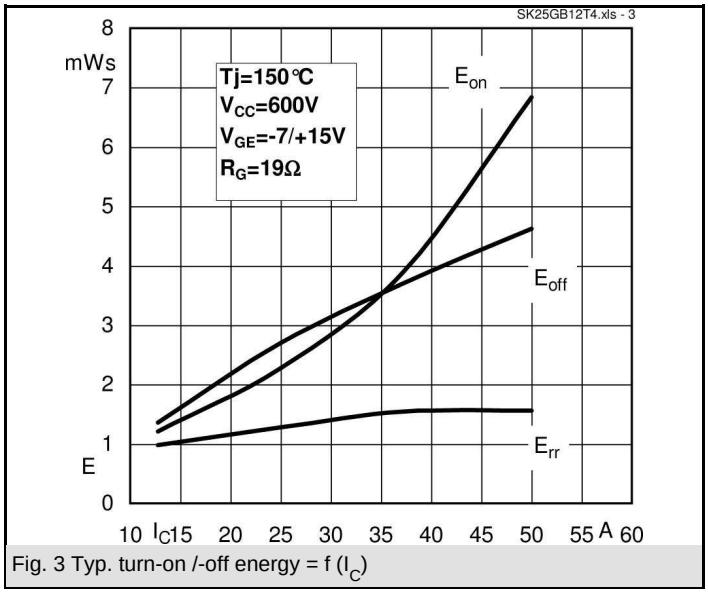


Fig. 3 Typ. turn-on /-off energy = f (I_C)

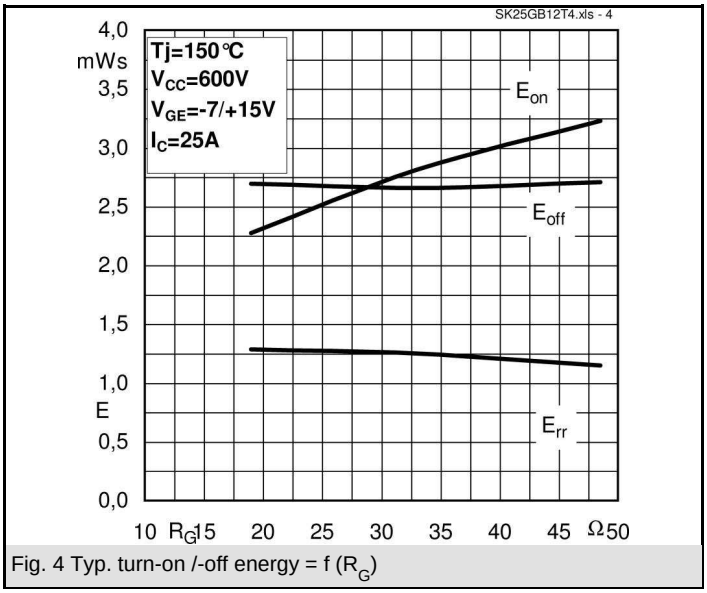


Fig. 4 Typ. turn-on /-off energy = f (R_G)

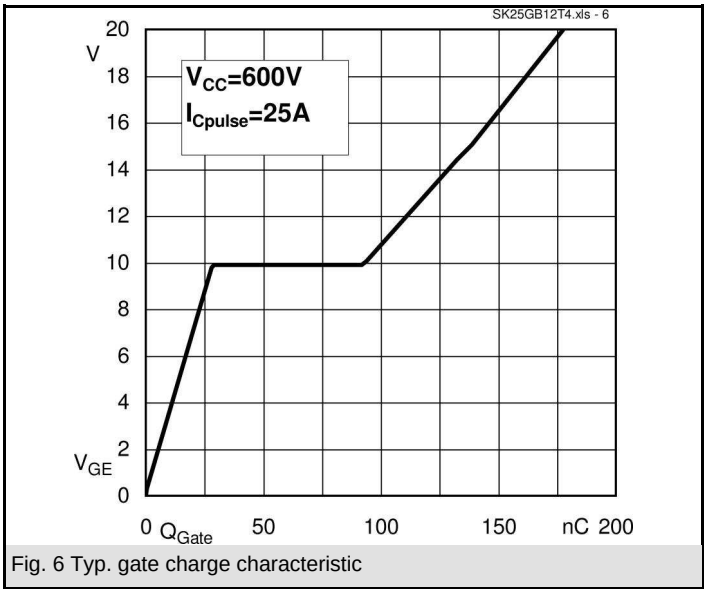


Fig. 6 Typ. gate charge characteristic

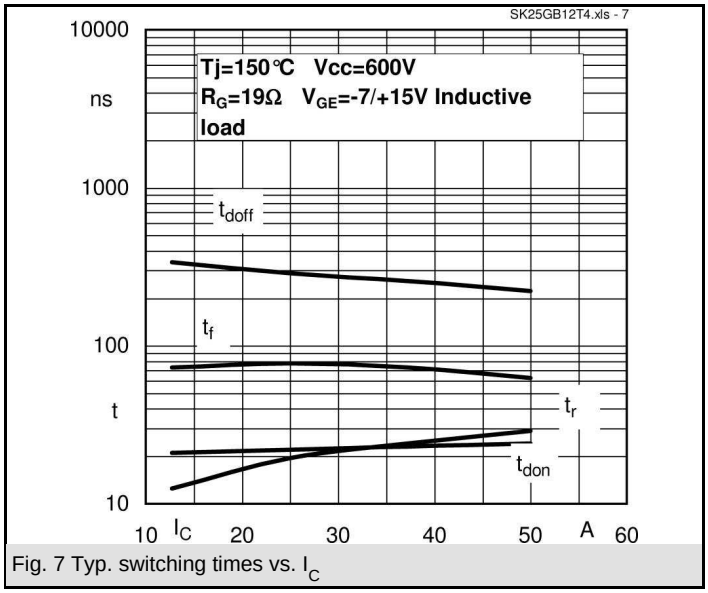


Fig. 7 Typ. switching times vs. I_C

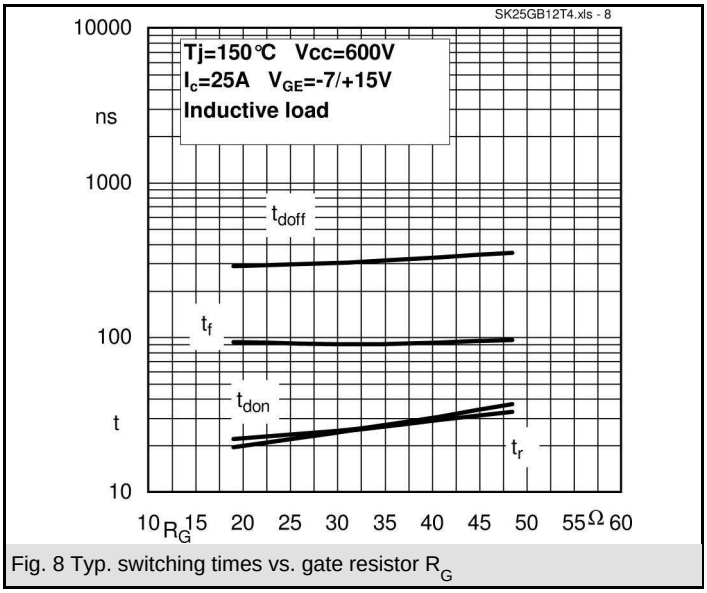


Fig. 8 Typ. switching times vs. gate resistor R_G

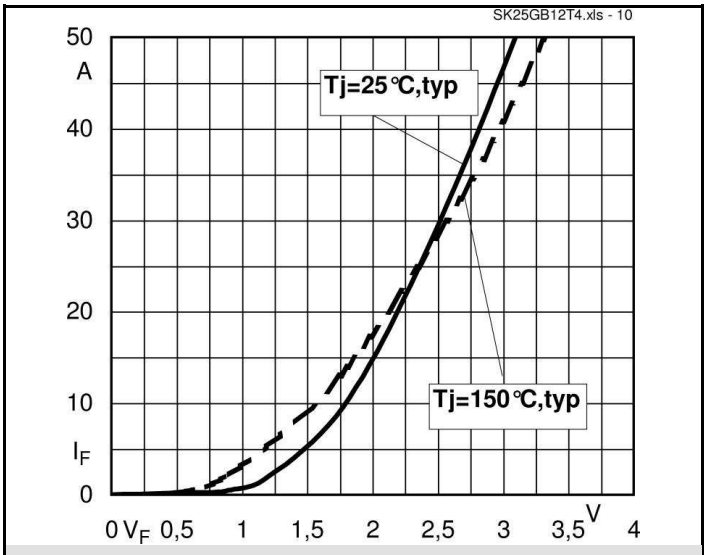
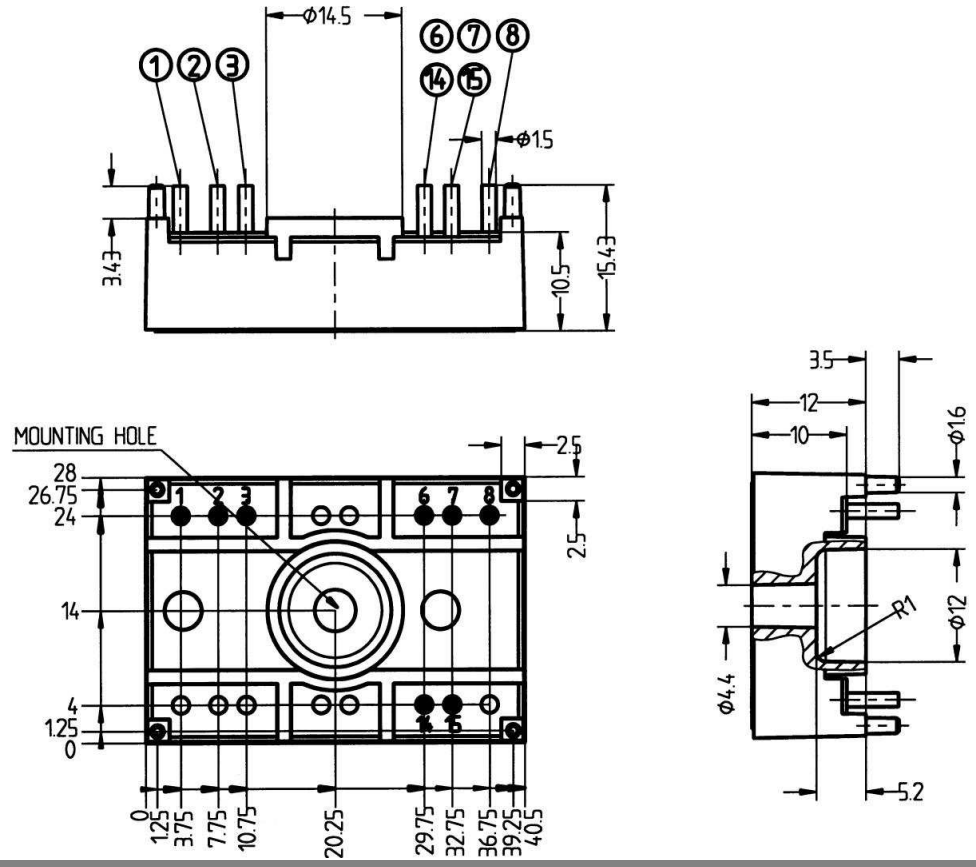
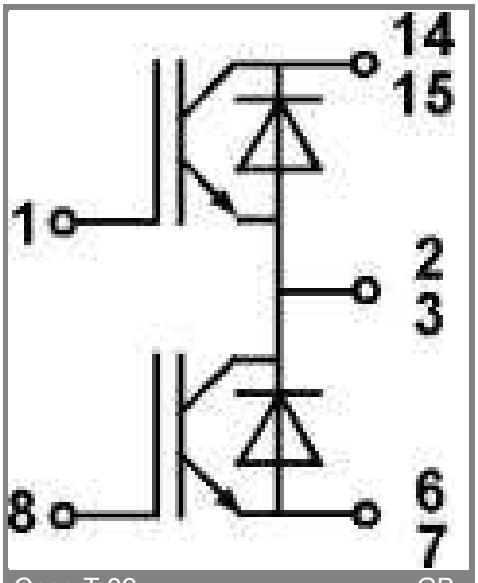


Fig. 10 CAL diode forward characteristic



Case T32 (Suggested hole diameter for solder pins and plastic mounting pins: 2mm)



Case T 32 GB

